

FEATURES:

- Improve EMI conduction characteristics
- Glass Passivated Chip Junction
- Reverse Voltage - 1000 V
- Forward Current - 4.0 A
- Fast reverse recovery time
- Designed for Surface Mount Application

MECHANICAL DATA

- Case: GBP
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 1.52g 0.05 oz

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbols	FGBP410	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	1000	V
Maximum RMS voltage	V_{RMS}	700	V
Maximum DC Blocking Voltage	V_{DC}	1000	V
Average Rectified Output Current	I_O	4.0	A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	I_{FSM}	100	A
Maximum Forward Voltage at 2.0 A	V_F	1.3	V
Maximum DC Reverse Current $T_a = 25^\circ\text{C}$ at Rated DC Blocking Voltage $T_a = 125^\circ\text{C}$	I_R	5.0 200	μA
Typical Junction Capacitance (Note1)	C_j	40	pF
Typical Thermal Resistance	$R_{\theta JA}$	45	$^\circ\text{C/W}$
Maximum Reverse Recovery Time (Note2)	t_{rr}	500	ns
Operating and Storage Temperature Range	T_j, T_{stg}	-55 ~ +150	$^\circ\text{C}$

Note: 1. Measured at 1MHz and applied reverse voltage of 4 V D.C.

2. Measured with $I_F = 0.5\text{ A}$, $I_R = 1\text{ A}$, $t_{rr} = 0.25\text{ A}$.

Fig.1 Average Rectified Output Current Derating Curve

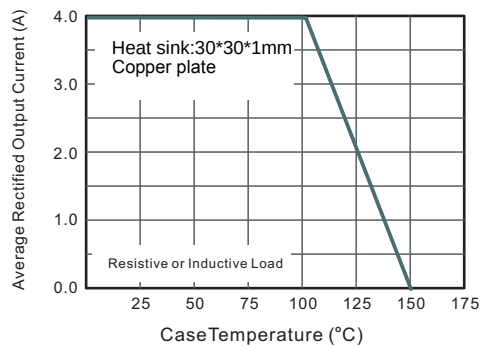


Fig.2 Typical Reverse Characteristics

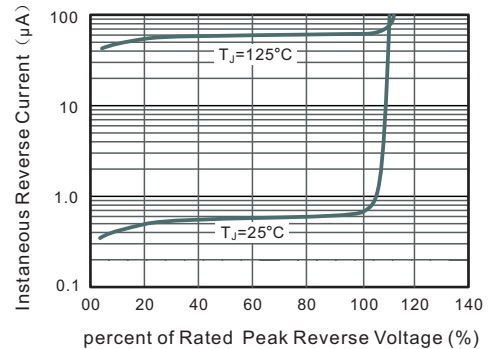


Fig.3 Typical Instantaneous Forward Characteristics

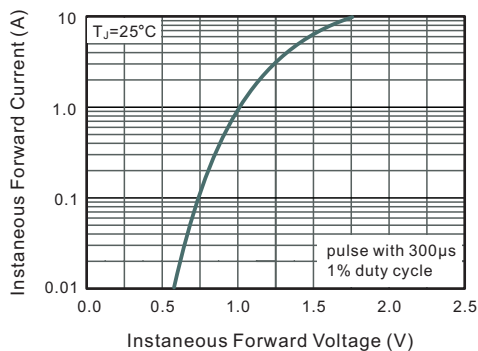
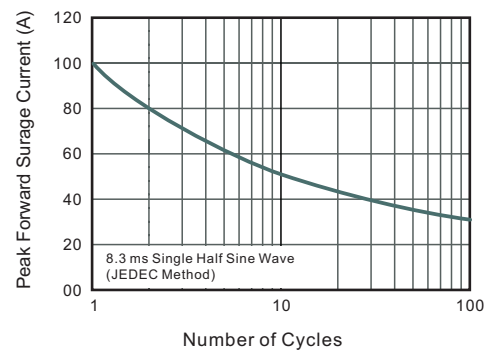
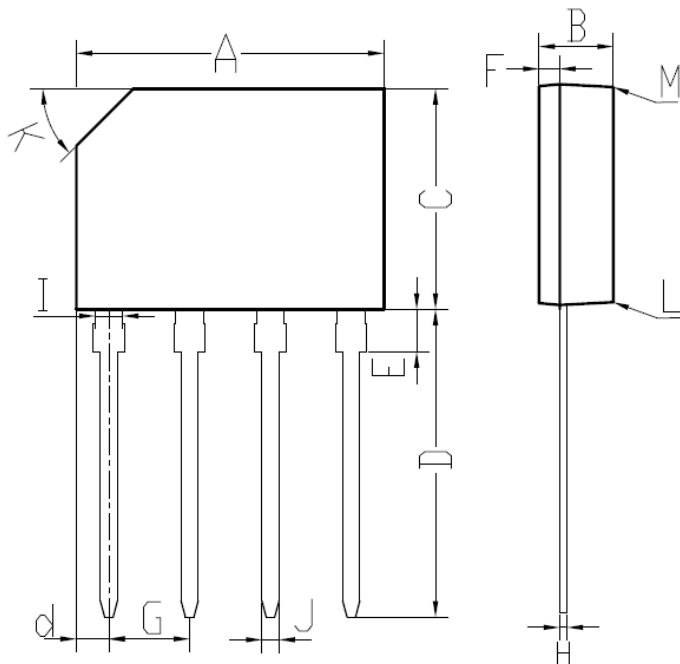


Fig.4 Maximum Non-Repetitive Peak Forward Surge Current



GBP Package Outline Dimensions



GBP		
DIM.	MIN.	MAX.
A	14.25	14.75
B	3.35	3.65
C	10.20	10.60
D	14.25	14.73
d	1.40	1.70
E	1.80	2.20
F	0.80	1.10
G	3.56	4.06
H	0.35	0.55
I	1.22	1.42
J	0.76	0.86
K	2.7 x 45° (Typ)	
L	#	3°
M	#	2°
All Dimensions in millimeter		